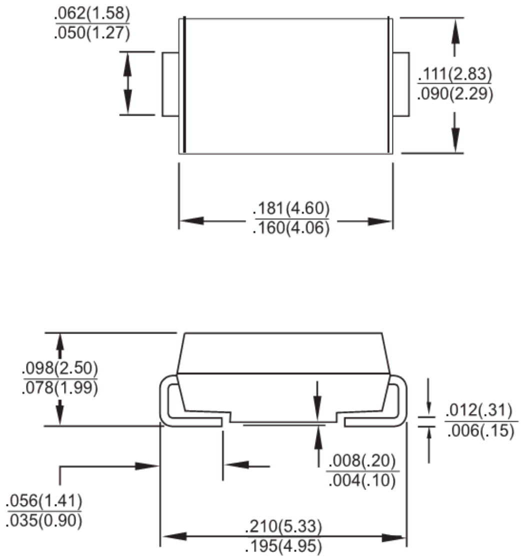
TAIWAN SEMICONDUCTOR

RoHS COMPLIANCE

US1A - US1M

1.0AMP. High Efficient Surface Mount Rectifiers

SMA/DO-214AC



Dimensions in inches and (millimeters)

Features

- ✧ Glass passivated chip junction
- ✧ For surface mounted application
- ✧ Low profile package
- ✧ Built-in strain relief
- ✧ Ideal for automated placement
- ✧ Easy pick and place
- ✧ Ultrafast recovery time for high efficiency
- ✧ Low forward voltage, low power loss
- ✧ High temperature soldering guaranteed: 260℃/10 seconds on terminals
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Case: Molded plastic
- ✧ Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- ✧ Polarity: Indicated by cathode band
- ✧ Weight: 0.064 grams

Marking Diagram

US1X = Specific Device Code
G = Green Compound
Y = Year
WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	US1A	US1B	US1D	US1G	US1J	US1K	US1M	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	1.0				1.7			V
Maximum Reverse Current @ Rated VR T_A=25 ℃ T_A=125 ℃	I_R	5 150							uA
Maximum Reverse Recovery Time (Note 2)	Trr	50				75			nS
Typical Junction Capacitance (Note 3)	Cj	15				10			pF
Typical Thermal Resistance	$R_{\theta jA}$ $R_{\theta jL}$	75 27							^{O}C/W
Operating Temperature Range	T_J	- 55 to + 150							^{O}C
Storage Temperature Range	T_{STG}	- 55 to + 150							^{O}C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

Version:G11

RATINGS AND CHARACTERISTIC CURVES (US1A THRU US1M)

FIG.1 MAXIMUM FORWARD CURRENT DERATING CURVE

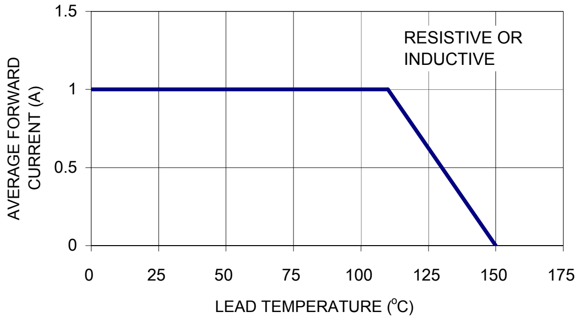


FIG. 2 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

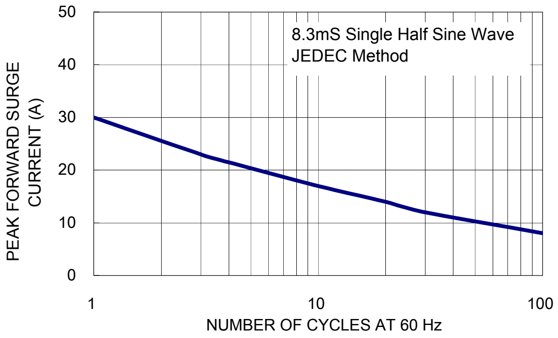


FIG. 3 TYPICAL FORWARD CHARACTERISRICS

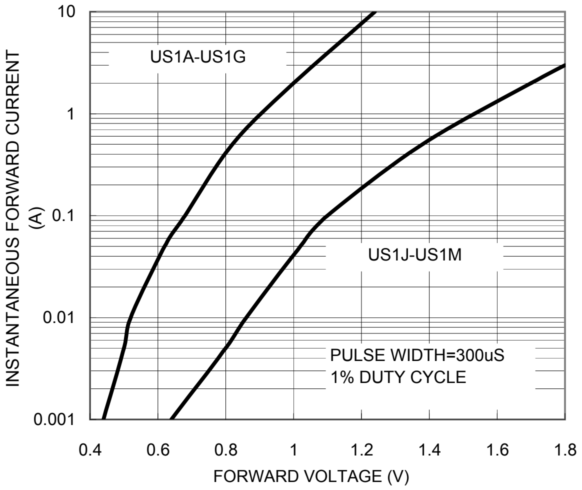


FIG. 4 TYPICAL REVERSE CHARACTERISTICS

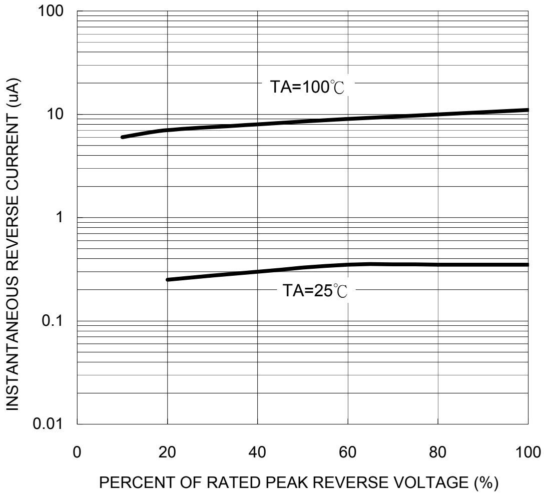


FIG. 5 TYPICAL JUNCTION CAPACITANCE

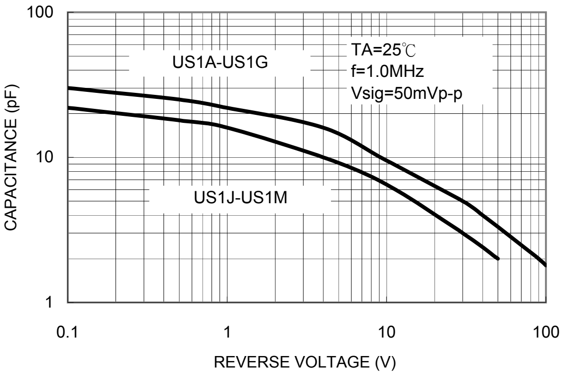


FIG. 6 TYPICAL TRANSIENT THERMAL IMPEDANCE

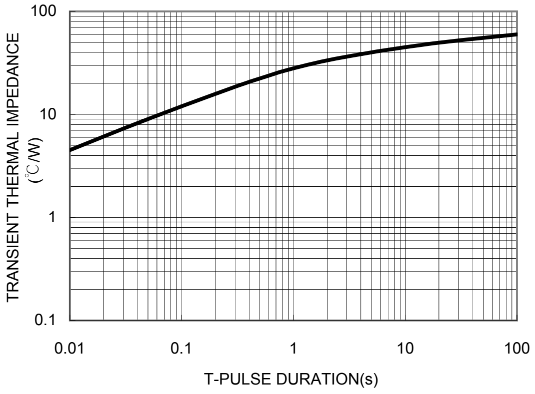
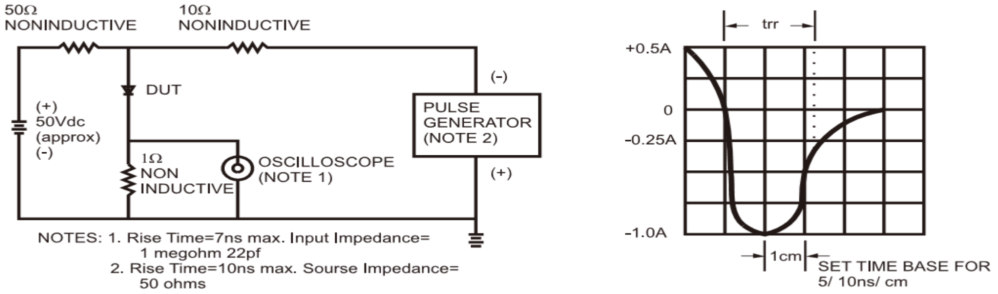


FIG.7- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



NOTES: 1. Rise Time=7ns max. Input Impedance=
1 megohm 22pf
2. Rise Time=10ns max. Sourse Impedance=
50 ohms